

A-9837E PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Lars Ivar SAMUELSON et al.

Appln. No.: 10/613,071

Group Art Unit: 2811

Filed: July 7, 2003

For: NANOSTRUCTURES AND METHODS FOR MANUFACTURING

THE SAME

INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any assertion as to materiality or prior art effect, the documents listed on the attached Form PTO-1449 are hereby cited.

Documents AA-AB, AE, AJ, AO, QD, and TH-TK on the attached List were cited in the International Search Report (copy attached) of counterpart PCT Application No. PCT/GB2004/000037.

Respectfully submitted,

MWS:1mb

Miles & Stockbridge P.C. 1751 Pinnacle Drive, Suite 500 McLean, Virginia 22102-3833 (703) 903-9000

September 29, 2004

Reg. No. 31,568

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Page 6 of 20

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Page 19 of 20

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Page 20 of 20

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